2CL2F 100mA 8.0kV

High Voltage Silicon Rectifier Diode

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. Small volume.
3. Low frequency.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Rectifier for high voltage power supply.
2. High voltage transformer rectifier.
3. Microwave equipment.
4. Other.

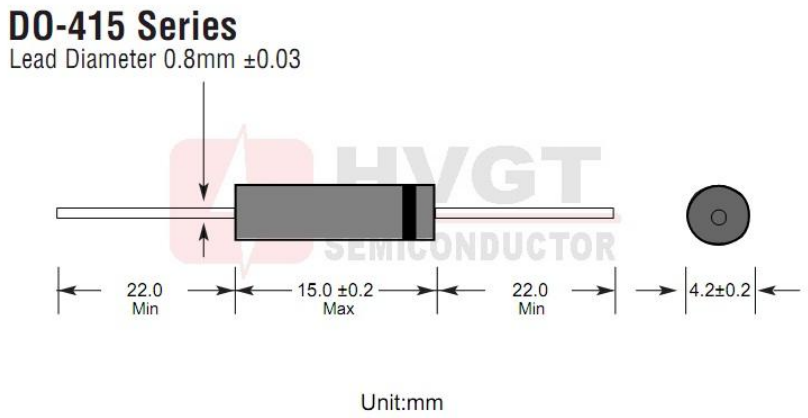
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.65 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) **HVGT NAME: DO-415**



MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C	8.0	kV
Non-Repetitive Peak Renerse Voltage	V_{RSM}	T_A=25°C	--	kV
Average Forward Current Maximum	I_{FAVM}	T_A=40°C	100	mA
		T_{OIL}=55°C	220	mA
Non-Repetitive Forward Surge Current	I_{FSM}	T_A=25°C; 50Hz Half-Sine Wave; 8.3mS	20	A
Junction Temperature	T_J		125	°C
Allowable Operation Case Temperature	Tc		-40~+125	°C
Storage Temperature	T_{STG}		-40~+125	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	10	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	2.0	uA
	I_{R2}	at 100°C; at V_{RRM}	40	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	--	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	--	pF

Fig 1

Forward Current Derating Curve

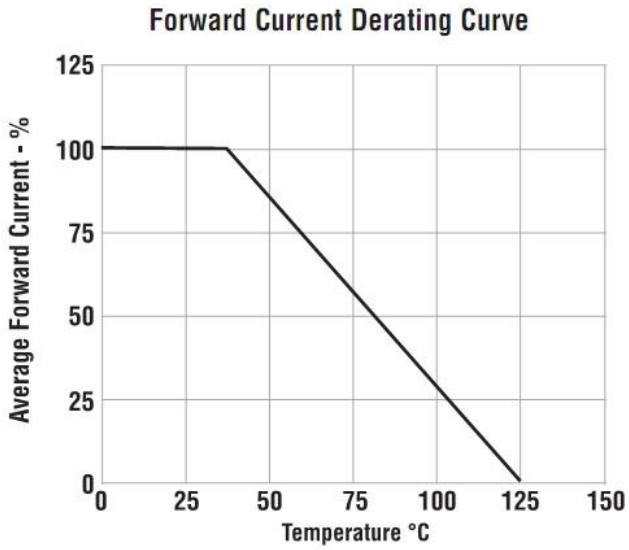
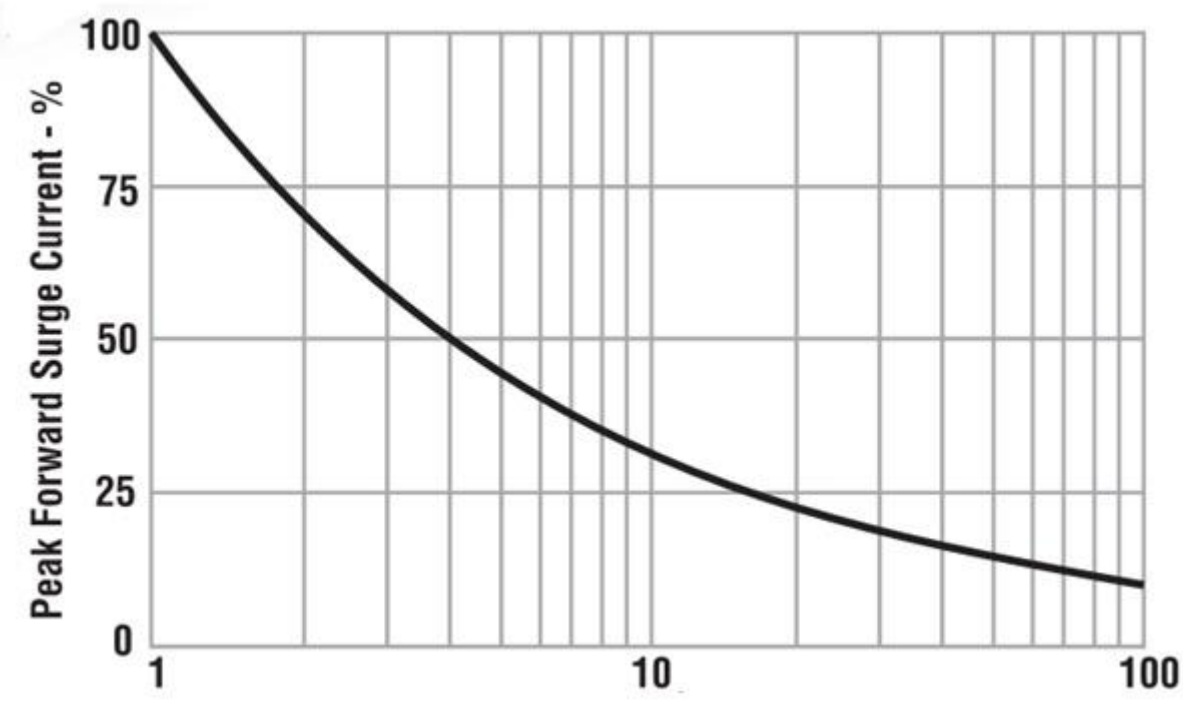


Fig 2

Non-Repetitive Surge Current



Cycles (50Hz)

Marking	Type	Code	Cathode Mark
	2CL2F	2CL2F HVGT	